

# Piezoresistive Pressure Sensor, Shell

# Introduction

Piezoresistive pressure sensors were some of the first MEMS devices to be commercialized. Compared to capacitive pressure sensors, they are simpler to integrate with electronics, their response is more linear and they are inherently shielded from RF noise. They do, however, usually require more power during operation and the fundamental noise limits of the sensor are higher than their capacitive counterparts. Historically, piezoresistive devices have been dominant in the pressure sensor market.

This example considers the design of the MPX100 series pressure sensors originally manufactured by Motorola Inc. (now Freescale Semiconductor, Inc.). Although the sensor is no longer in production, a detailed analysis of its design is given in Ref. 1, and an archived data sheet is available from Freescale Semiconductor Inc. (Ref. 2).

**Note:** This model requires the MEMS Module and the Structural Mechanics Module.

# Model Definition

The model consists square membrane with side 1 mm and thickness 20 µm, supported around its edges by region 0.1mm wide, which is intended to represent the remainder of the wafer. The supporting region is fixed on its underside (representing a connection to the thicker handle of the device die). Near to one edge of the membrane, an X-shaped piezoresistor (or Xducer<sup>TM</sup>)<sup>1</sup> and part of its associated interconnects are visible. The geometry is shown in Figure 1.

The piezoresistor is assumed to have a uniform p-type dopant density of  $1.32 \times 10^{19}$  cm<sup>-3</sup> and a thickness of 400 nm. The interconnects are assumed to have the same thickness but a dopant density of  $1.45 \times 10^{20}$  cm<sup>-3</sup>. Only a part of the interconnects is included in the geometry because their conductivity is sufficiently high that they do not contribute to the voltage output of the device (in practice, the interconnects would also be thicker in addition to having a higher conductivity but this also has little effect on the solution).

The edges of the die are aligned with the  $\{110\}$  directions of the silicon. The die edges are also aligned with the global X- and Y-axes in the COMSOL Multiphysics model. The piezoresistor is oriented at 45 to the die edge, and so lies in the [100] direction of the

<sup>1.</sup> Xducer™ is believed to be a trademark of Freescale Semiconductor, Inc. f/k/a Motorola, Inc. Neither Freescale Semiconductor, Inc. nor Motorola, Inc. has in any way provided any sponsorship or endorsement of, nor do they have any connection or involvement with, COMSOL Multiphysics software or this model.

crystal. In the COMSOL Multiphysics model, a coordinate system rotated 45 about the global *Z*-axis is added to define the orientation of the crystal.

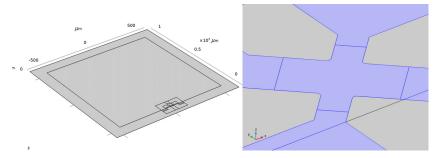


Figure 1: Left: Model geometry. Right: Detail showing the piezoresistor geometry.

# **DEVICE PHYSICS AND EQUATIONS**

The conductivity of the Xducer<sup>TM</sup> sensor changes when the membrane in its vicinity is subject to an applied stress. This effect is known as the piezoresistance effect and is usually associated with semiconducting materials. In semiconductors, piezoresistance results from the strain induced alteration of the material's band structure, and the associated changes in carrier mobility and number density. The relation between the electric field, **E**, and the current, **J**, within a piezoresistor is:

$$\mathbf{E} = \rho \cdot \mathbf{J} + \Delta \rho \cdot \mathbf{J} \tag{1}$$

where  $\rho$  is the resistivity and  $\Delta \rho$  is the induced change in the resistivity. In the general case both  $\rho$  and  $\Delta \rho$  are rank 2 tensors (matrices). The change in resistance is related to the stress,  $\sigma$ , by the constitutive relationship:

$$\Delta \rho = \Pi \cdot \sigma \tag{2}$$

where  $\Pi$  is the piezoresistance tensor (SI units: Pa<sup>-1</sup> $\Omega$ m), a material property. Note that the COMSOL Multiphysics definition of  $\Pi$  includes the resistivity in each element of the tensor, rather than having a scalar multiple outside of  $\Pi$  (which is possible only for materials with isotropic conductivity).  $\Pi$  is in this case a rank 4 tensors, however it can be represented as a matrix if the resistivity and stress are converted to vectors within a reduced subscript notation. Within the Voigt notation used by COMSOL Multiphysics for this purpose, Equation 2 becomes:

$$\begin{bmatrix} \Delta \rho_{xx} \\ \Delta \rho_{yy} \\ \Delta \rho_{zz} \\ \Delta \rho_{yz} \\ \Delta \rho_{yz} \\ \Delta \rho_{xz} \\ \Delta \rho_{xz} \\ \Delta \rho_{xz} \\ \Delta \rho_{xy} \end{bmatrix} = \begin{bmatrix} \Pi_{11} \ \Pi_{12} \ \Pi_{13} \ \Pi_{14} \ \Pi_{15} \ \Pi_{16} \\ \Pi_{21} \ \Pi_{22} \ \Pi_{23} \ \Pi_{24} \ \Pi_{25} \ \Pi_{26} \\ \Pi_{31} \ \Pi_{32} \ \Pi_{33} \ \Pi_{34} \ \Pi_{35} \ \Pi_{36} \\ \Pi_{41} \ \Pi_{42} \ \Pi_{43} \ \Pi_{44} \ \Pi_{45} \ \Pi_{46} \\ \Pi_{51} \ \Pi_{52} \ \Pi_{53} \ \Pi_{54} \ \Pi_{55} \ \Pi_{56} \\ \Delta \rho_{xy} \end{bmatrix} \cdot \begin{bmatrix} \sigma^{xx} \\ \sigma^{yy} \\ \sigma^{zz} \\ \sigma^{yz} \\ \sigma^{xz} \\ \sigma^{xz} \\ \sigma^{xy} \end{bmatrix}$$

$$(3)$$

The  $\Delta p$  vector computed from Equation 3 is assembled into matrix form in the following manner in Equation 1:

$$\begin{bmatrix} E_{x} \\ E_{y} \\ E_{z} \end{bmatrix} = \begin{bmatrix} \rho_{xx} & \rho_{xy} & \rho_{xz} \\ \rho_{xy} & \rho_{yy} & \rho_{yz} \\ \rho_{xz} & \rho_{yz} & \rho_{zz} \end{bmatrix} \cdot \begin{bmatrix} J_{x} \\ J_{y} \\ J_{z} \end{bmatrix} + \begin{bmatrix} \Delta \rho_{xx} & \Delta \rho_{xy} & \Delta \rho_{xz} \\ \Delta \rho_{xy} & \Delta \rho_{yy} & \Delta \rho_{yz} \end{bmatrix} \cdot \begin{bmatrix} J_{x} \\ J_{y} \\ J_{z} \end{bmatrix}$$

$$\Delta \rho_{xz} & \Delta \rho_{yz} & \Delta \rho_{zz} \end{bmatrix} \cdot \begin{bmatrix} J_{x} \\ J_{y} \\ J_{z} \end{bmatrix}$$

$$(4)$$

Silicon has cubic symmetry, and as a result the  $\Pi$  matrix can be described in terms of three independent constants in the following manner:

$$\Pi = \begin{bmatrix} \Pi_{11} \ \Pi_{12} \ \Pi_{12} \ 0 & 0 & 0 \\ \Pi_{12} \ \Pi_{22} \ \Pi_{12} \ 0 & 0 & 0 \\ \Pi_{12} \ \Pi_{12} \ \Pi_{33} \ 0 & 0 & 0 \\ 0 & 0 & 0 \ \Pi_{44} \ 0 & 0 \\ 0 & 0 & 0 & 0 \ \Pi_{44} \ 0 \\ 0 & 0 & 0 & 0 & 0 \ \Pi_{44} \end{bmatrix}$$

For p-type silicon the  $\Pi_{44}$  constant is two orders of magnitude larger than either the  $\Pi_{11}$  or the  $\Pi_{12}$  coefficients. The  $\Pi_{66}$  element (which is equal in magnitude to the  $\Pi_{44}$  element) couples the  $\sigma_{xy}$  shear stress, with the  $\Delta\rho_{xy}$  off-diagonal term in the change in resistivity matrix. In turn,  $\Delta\rho_{xy}$  couples a current in the x-direction to an induced electric field in the y-direction (and vice versa). This is the principle of the Xducer  $^{TM}$  transducer. An applied voltage (typically 3 V (Ref. 2)) across the [100] orientated arm of the X produces a current (typically 6 mA (Ref. 2)) down this arm. Shear stresses are present in the Xducer  $^{TM}$  as a result of the pressure induced deformation of the diaphragm in which it is implanted. Through the piezoresistance effect, these shear stresses cause an electric field or potential gradient transverse to the direction of current flow, in the [010] arm of the X. Across the

width of the transducer, the potential gradient sums up to produce an induced voltage difference between the [010] arms of the X. According to the device data sheet, under normal operating conditions a 60 mV potential difference is generated from a 100 kPa applied pressure with a 3 V applied bias (Ref. 2)).

The situation is complicated somewhat by the detailed current distribution within the device, since the voltage sensing elements increase the width of the current carrying silicon wire locally, leading to a "short circuit" effect (Ref. 3) or a spreading out of the current into the sense arms of the X.

The Piezoresistance interfaces available with the MEMS Module solve Equation 3 and an inverse form of Equation 4, together with the equations of structural mechanics. In this model the *Piezoresistance*, *Boundary Currents* interface is used to model the structural equations on the domain level and to solve the electrical equations on a thin layer coincident with a boundary in the model geometry.

# Results and Discussion

Figure 2 shows the displacement of the diaphragm as a result of a 100 kPa pressure difference applied to the membrane, at its center the displacement is 1.2  $\mu$ m. A simple isotropic model for the deform displacement given in Ref. 1 predicts an order of magnitude value for the displacement of 4  $\mu$ m (assuming a Young's Modulus of 170 GPa and a Poisson's ratio of 0.06). The agreement is reasonable considering the limitations of the analytic model, which is derived by a crude variational guess. A more accurate value for the shear stress in local co-ordinates at the midpoint of the diaphragm edge is given in Ref. 1 as:

$$\sigma^{l, 12} = 0.141 \left(\frac{L}{H}\right)^2 P$$

where P is the applied pressure, L is the length of the diaphragm edge and H is the diaphragm thickness. This equation predicts the magnitude of the local shear stress to be 35 MPa, in good agreement with the minimum value shown in Figure 3, which is 35 MPa. Theoretically the shear stress should be maximal at the midpoint of the edge of the diaphragm. Figure 4 shows the shear stress along the edge in the model. This shows a maximum magnitude of 38 MPa at the center of each of the two edges along which the plot is made.



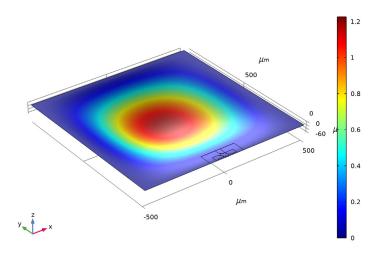


Figure 2: Diaphragm displacement as a result of a 100 kPa applied pressure.

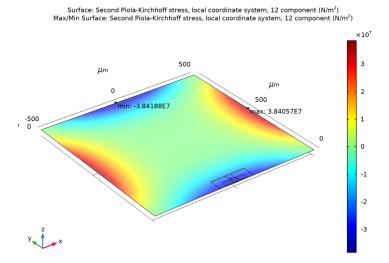


Figure 3: Shear stress, shown in the local coordinate system of the piezoresistor (rotated  $45^{\circ}$  about the z-axis of the global system). The shear stress is has its highest magnitude close to the piezoresistor with a value of approximately -35 MPa.

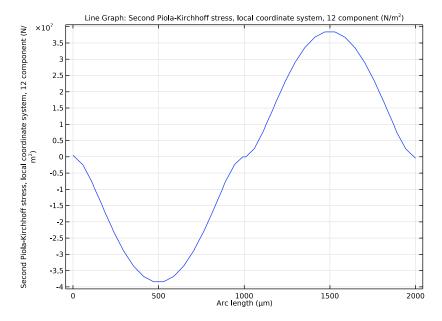


Figure 4: Plot of the local shear stress along two edges of the diaphragm.

The output of the model during normal operation shows good agreement with the manufacturer's data sheet, given that the device dimensions and doping levels have been guessed. With an applied bias of 3 V a typical operating current of 5.9 mA is obtained (c.f. the current quoted in Ref. 2 of 6 mA). The model produces an output voltage of 54 mV, similar to the actual device output of 60 mV quoted in Ref. 2. The detailed current and voltage distribution within the Xducer<sup>TM</sup> is shown in Figure 5. There is clear evidence of the current flow 'spreading out' into the sense electrodes (which are narrower), a phenomena described in Ref. 3 as the "short circuit" effect. The asymmetry in the potential, which is induced by the piezoresistive effect, is also apparent in the figure.

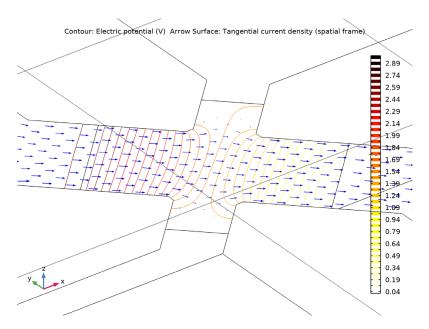


Figure 5: Arrows: Current density, Contours: Electric Potential, for a device driven by a 3 V bias with an applied pressure of 100 kPa.

# References

- 1. S.D. Senturia, "A Piezoresistive Pressure Sensor", Microsystem Design, chapter 18, Springer, 2000.
- 2. Motorola Semiconductor MPX100 series technical data, document: MPX100/D, 1998 (available from Freescale Semiconductor, Inc at http://www.freescale.com).
- 3. M. Bao, Analysis and Design Principles of MEMS Devices, Elsevier B. V., 2005.

Application Library path: MEMS Module/Sensors/ piezoresistive\_pressure\_sensor\_shell

# Modeling Instructions

From the File menu, choose New.

#### NEW

In the New window, click Model Wizard.

# MODEL WIZARD

- I In the Model Wizard window, click **3D**.
- 2 In the Select Physics tree, select Structural Mechanics>Electromagnetics-Structure Interaction>Piezoresistivity>Piezoresistivity, Shell.
- 3 Click Add.
- 4 Click 🔁 Study.
- 5 In the Select Study tree, select General Studies>Stationary.
- 6 Click M Done.

#### GEOMETRY I

- I In the Model Builder window, under Component I (compl) click Geometry I.
- 2 In the Settings window for Geometry, locate the Units section.
- 3 From the Length unit list, choose  $\mu m$ .

For convenience, the device geometry is inserted from an existing file. You can read the instructions for creating the geometry in the Appendix — Geometry Modeling Instructions.

- 4 In the Geometry toolbar, click Insert Sequence.
- **5** Browse to the model's Application Libraries folder and double-click the file piezoresistive pressure sensor shell geom sequence.mph.
- 6 In the Geometry toolbar, click **Build All**.

The dimensions of this geometry are given in micrometers, so you need to change the length unit accordingly.

#### DEFINITIONS

# Piezoresistor

- I In the **Definitions** toolbar, click **\( \frac{1}{2} \) Explicit**.
- 2 In the Settings window for Explicit, type Piezoresistor in the Label text field.
- 3 Locate the Input Entities section. From the Geometric entity level list, choose Boundary.
- 4 Select Boundary 9 only.

# Connections

I Right-click Piezoresistor and choose Duplicate.

- 2 In the Settings window for Explicit, type Connections in the Label text field.
- 3 Locate the Input Entities section. Click Clear Selection.
- **4** Select Boundaries 3, 5, 6, 8, 13–15, and 18 only.

# Membrane

- I In the **Definitions** toolbar, click **Box**.
- 2 In the Settings window for Box, type Membrane in the Label text field.
- 3 Locate the Geometric Entity Level section. From the Level list, choose Boundary.
- **4** Locate the **Box Limits** section. In the **x minimum** text field, type -501.
- 5 In the x maximum text field, type 501.
- 6 In the y minimum text field, type -30.
- 7 In the y maximum text field, type 1000.
- 8 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.

# Model boundaries

- I In the **Definitions** toolbar, click **Holion**.
- 2 In the Settings window for Union, type Model boundaries in the Label text field.
- 3 Locate the Geometric Entity Level section. From the Level list, choose Boundary.
- 4 Locate the Input Entities section. Under Selections to add, click + Add.
- 5 In the Add dialog box, in the Selections to add list, choose Connections and Membrane.
- 6 Click OK.

#### Electric currents

- I Right-click Model boundaries and choose Duplicate.
- 2 In the Settings window for Union, type Electric currents in the Label text field.
- 3 Locate the Input Entities section. In the Selections to add list, select Membrane.
- 4 Under Selections to add, click **Delete**.
- 5 Under Selections to add, click + Add.
- 6 In the Add dialog box, select Piezoresistor in the Selections to add list.
- 7 Click OK.

# Fixed Edges

- I In the **Definitions** toolbar, click **Adjacent**.
- 2 In the Settings window for Adjacent, type Fixed Edges in the Label text field.

- 3 Locate the Input Entities section. From the Geometric entity level list, choose Boundary.
- 4 Under Input selections, click + Add.
- 5 In the Add dialog box, select Membrane in the Input selections list.
- 6 Click OK.
- 7 In the Settings window for Adjacent, locate the Output Entities section.
- 8 From the Geometric entity level list, choose Adjacent edges.

# Fixed Boundaries

- I In the **Definitions** toolbar, click **Difference**.
- 2 In the Settings window for Difference, locate the Geometric Entity Level section.
- 3 From the Level list, choose Boundary.
- 4 Locate the Input Entities section. Under Selections to add, click + Add.
- 5 In the Add dialog box, select Model boundaries in the Selections to add list.
- 6 Click OK.
- 7 In the Settings window for Difference, locate the Input Entities section.
- 8 Under Selections to subtract, click Add.
- 9 In the Add dialog box, select Membrane in the Selections to subtract list.
- IO Click OK.
- II In the Settings window for Difference, type Fixed Boundaries in the Label text field.

# Rotated System 2 (sys2)

- I In the **Definitions** toolbar, click **Coordinate Systems** and choose **Rotated System**.
- 2 In the Settings window for Rotated System, locate the Rotation section.
- 3 Find the Euler angles (Z-X-Z) subsection. In the  $\alpha$  text field, type -45[deg].

#### ADD MATERIAL

- I In the Home toolbar, click 4 Add Material to open the Add Material window.
- 2 Go to the Add Material window.
- 3 In the tree, select Piezoresistivity>n-Silicon (single-crystal, lightly doped).
- **4** Click **Add to Component** in the window toolbar.
- 5 In the tree, select Piezoresistivity>p-Silicon (single-crystal, lightly doped).
- **6** Click **Add to Component** in the window toolbar.
- 7 In the Home toolbar, click Radd Material to close the Add Material window.

#### MATERIALS

p-Silicon (single-crystal, lightly doped) (mat2)

- I In the Settings window for Material, locate the Geometric Entity Selection section.
- **2** From the **Selection** list, choose **Electric currents**.

# SHELL (SHELL)

- I In the Model Builder window, under Component I (compl) click Shell (shell).
- 2 In the Settings window for Shell, locate the Boundary Selection section.
- 3 From the Selection list, choose Model boundaries.

Thickness and Offset I

- I In the Model Builder window, under Component I (compl)>Shell (shell) click Thickness and Offset 1.
- 2 In the Settings window for Thickness and Offset, locate the Thickness and Offset section.
- 3 In the d text field, type 20 [um].

Linear Elastic Material I

- I In the Model Builder window, click Linear Elastic Material I.
- 2 In the Settings window for Linear Elastic Material, locate the Linear Elastic Material section.
- 3 From the Solid model list, choose Anisotropic.
- 4 From the Material data ordering list, choose Voigt (11, 22, 33, 23, 13, 12).

Shell Local System 1

- I In the Model Builder window, expand the Linear Elastic Material I node, then click Shell Local System 1.
- 2 In the Settings window for Shell Local System, locate the Coordinate System Selection section.
- 3 From the Coordinate system list, choose Rotated System 2 (sys2).

Fixed Constraint I

- I In the Physics toolbar, click **Edges** and choose **Fixed Constraint**.
- 2 In the Settings window for Fixed Constraint, locate the Edge Selection section.
- **3** From the **Selection** list, choose **Fixed Edges**.

Fixed Constraint 2

I In the Physics toolbar, click **Boundaries** and choose Fixed Constraint.

- 2 In the Settings window for Fixed Constraint, locate the Boundary Selection section.
- 3 From the Selection list, choose Fixed Boundaries.

#### Face Load 1

- I In the Physics toolbar, click **Boundaries** and choose Face Load.
- 2 In the Settings window for Face Load, locate the Boundary Selection section.
- 3 From the Selection list, choose Membrane.
- 4 Locate the Force section. From the Load type list, choose Pressure.
- **5** In the p text field, type 100[kPa].

# ELECTRIC CURRENTS, SINGLE LAYER SHELL (ECS)

- I In the Model Builder window, under Component I (compl) click Electric Currents, Single Layer Shell (ecs).
- 2 In the Settings window for Electric Currents, Single Layer Shell, locate the Boundary Selection section.
- 3 Click Clear Selection.
- 4 From the Selection list, choose Electric currents.
- **5** Locate the **Shell Thickness** section. In the  $d_s$  text field, type 0.4[um].
- **6** Click the **Show More Options** button in the **Model Builder** toolbar.
- 7 In the Show More Options dialog box, in the tree, select the check box for the node Physics>Advanced Physics Options.
- 8 Click OK.

# Current Conservation I

- I In the Model Builder window, under Component I (compl)>Electric Currents,
  Single Layer Shell (ecs) click Current Conservation I.
- 2 In the Settings window for Current Conservation, click to expand the Model Inputs section.
- **3** In the  $n_d$  text field, type 1.45e20[1/cm<sup>3</sup>].
- 4 Locate the Coordinate System Selection section. From the Coordinate system list, choose Rotated System 2 (sys2).

# Piezoresistive Material I

- I In the Model Builder window, click Piezoresistive Material I.
- 2 In the Settings window for Piezoresistive Material, locate the Boundary Selection section.
- 3 From the Selection list, choose Piezoresistor.

- **4** Locate the **Model Input** section. In the  $n_d$  text field, type 1.32e19[1/cm<sup>3</sup>].
- 5 Locate the Coordinate System Selection section. From the Coordinate system list, choose Rotated System 2 (sys2).

#### Ground 1

- I In the Physics toolbar, click **Edges** and choose **Ground**.
- **2** Select Edge 70 only.

# Terminal I

- I In the Physics toolbar, click Edges and choose Terminal.
- **2** Select Edges 11 and 13 only.
- 3 In the Settings window for Terminal, locate the Terminal section.
- 4 From the Terminal type list, choose Voltage.
- **5** In the  $V_0$  text field, type 3.

# Terminal 2

- I In the Physics toolbar, click Edges and choose Terminal.
- **2** Select Edge 7 only.

#### Terminal 3

- I In the Physics toolbar, click Edges and choose Terminal.
- 2 Select Edges 72 and 73 only.

# MESH I

- I In the Model Builder window, under Component I (compl) click Mesh I.
- 2 In the Settings window for Mesh, locate the Mesh Settings section.
- 3 From the Sequence type list, choose User-controlled mesh.

# Size

- I In the Model Builder window, under Component I (compl)>Mesh I click Size.
- 2 In the Settings window for Size, locate the Element Size section.
- 3 Click the **Custom** button.
- 4 Locate the Element Size Parameters section. In the Maximum element size text field, type 60.
- 5 In the Minimum element size text field, type 0.5.

#### Size 1

I Right-click Size and choose Duplicate.

- 2 In the Settings window for Size, locate the Geometric Entity Selection section.
- 3 From the Geometric entity level list, choose Boundary.
- **4** From the **Selection** list, choose **Piezoresistor**.
- 5 Locate the Element Size Parameters section. In the Maximum element size text field, type 2.
- 6 In the Minimum element size text field, type 0.1.

# Size 2

- I Right-click Size I and choose Duplicate.
- 2 In the Settings window for Size, locate the Geometric Entity Selection section.
- **3** From the **Selection** list, choose **Connections**.
- 4 Locate the Element Size Parameters section. In the Maximum element size text field, type 6.

#### Size 3

- I Right-click Size 2 and choose Duplicate.
- 2 In the Settings window for Size, locate the Geometric Entity Selection section.
- 3 From the Geometric entity level list, choose Edge.
- **4** Select Edges 27, 29, 38–44, and 51–53 only.
- 5 Locate the **Element Size Parameters** section. In the **Maximum element size** text field, type 0.4.

# Free Triangular I

- I In the Model Builder window, right-click Free Triangular I and choose Move Down.
- 2 Right-click Free Triangular I and choose Move Down.
- 3 Right-click Free Triangular I and choose Move Down.
- 4 In the Home toolbar, click **Compute**.

# RESULTS

# Stress (shell)

The default plots show the von Mises stress, the undeformed geometry and the electric potential. Now create a plot of the displacement to compare with Figure 2.

# Study I/Solution I (2) (soll)

- I In the Model Builder window, expand the Results>Datasets node.
- 2 Right-click Results>Datasets>Study I/Solution I (soll) and choose Duplicate.

#### Selection

- I In the Results toolbar, click has a Attributes and choose Selection.
- 2 In the Settings window for Selection, locate the Geometric Entity Selection section.
- 3 From the Geometric entity level list, choose Boundary.
- 4 From the Selection list, choose Membrane.

# Disblacement

- I In the Results toolbar, click **3D Plot Group**.
- 2 In the Settings window for 3D Plot Group, type Displacement in the Label text field.
- 3 Locate the Data section. From the Dataset list, choose Study I/Solution I (2) (soll).

# Surface I

- I Right-click **Displacement** and choose **Surface**.
- 2 In the Settings window for Surface, click Replace Expression in the upper-right corner of the Expression section. From the menu, choose Component I (compl)>Shell> Displacement>shell.disp - Displacement magnitude - m.

# Deformation I

- I Right-click Surface I and choose Deformation.
- 2 In the **Displacement** toolbar, click **Displacement** 1

Now create a plot of the shear stress in the local coordinate system of the piezoresistor, to compare with Figure 3.

# In-Plane Shear Stress (Local Coordinates)

- I In the Home toolbar, click **Add Plot Group** and choose **3D Plot Group**.
- 2 In the Settings window for 3D Plot Group, type In-Plane Shear Stress (Local Coordinates) in the Label text field.
- 3 Locate the Data section. From the Dataset list, choose Study I/Solution I (2) (soll).

# Surface 1

- I Right-click In-Plane Shear Stress (Local Coordinates) and choose Surface.
- 2 In the Settings window for Surface, click Replace Expression in the upper-right corner of the Expression section. From the menu, choose Component I (compl)>Shell>Stress> Second Piola-Kirchhoff stress, local coordinate system - N/m2>shell.SI12 - Second Piola-Kirchhoff stress, local coordinate system, 12 component.

# In-Plane Shear Stress (Local Coordinates)

In the Model Builder window, click In-Plane Shear Stress (Local Coordinates).

Max/Min Surface I

- I In the In-Plane Shear Stress (Local Coordinates) toolbar, click More Plots and choose Max/Min Surface.
- 2 In the Settings window for Max/Min Surface, click Replace Expression in the upper-right corner of the Expression section. From the menu, choose shell.SI12 Second Piola-Kirchhoff stress, local coordinate system, 12 component N/m².
- 3 In the In-Plane Shear Stress (Local Coordinates) toolbar, click **1** Plot.

#### TABLE

Go to the Table window.

Create a line plot of the shear stress in the local coordinate system of the piezoresistor, to compare with Figure 4.

#### RESULTS

In-Plane Shear Stress (Local Coordinate System)

- I In the Home toolbar, click **Add Plot Group** and choose ID Plot Group.
- 2 In the Settings window for ID Plot Group, type In-Plane Shear Stress (Local Coordinate System) in the Label text field.

Line Graph I

- I Right-click In-Plane Shear Stress (Local Coordinate System) and choose Line Graph.
- **2** Select Edges 6 and 76 only.
- 3 In the Settings window for Line Graph, click Replace Expression in the upper-right corner of the y-Axis Data section. From the menu, choose Component I (compl)>Shell>Stress> Second Piola-Kirchhoff stress, local coordinate system N/m²>shell.Sl12 Second Piola-Kirchhoff stress, local coordinate system, 12 component.

Now create a plot of the detailed current and voltage distribution, to compare with Figure 5.

Study I/Solution I (3) (soll)

In the Model Builder window, under Results>Datasets right-click Study 1/ Solution 1 (2) (sol1) and choose Duplicate.

Selection

I In the Model Builder window, expand the Study I/Solution I (3) (solI) node, then click Selection.

- 2 In the Settings window for Selection, locate the Geometric Entity Selection section.
- 3 From the Selection list, choose Piezoresistor.
- 4 Click Zoom to Selection.
- 5 From the Selection list, choose Electric currents.

# Current and Voltage

- I In the Home toolbar, click 📭 Add Plot Group and choose 3D Plot Group.
- 2 In the Settings window for 3D Plot Group, type Current and Voltage in the Label text field.
- 3 Locate the Data section. From the Dataset list, choose Study I/Solution I (3) (soll).

#### Contour I

- I Right-click Current and Voltage and choose Contour.
- 2 In the Settings window for Contour, locate the Expression section.
- **3** In the **Expression** text field, type V.
- **4** Locate the **Levels** section. In the **Total levels** text field, type 40.
- 5 Locate the Coloring and Style section. From the Color table list, choose Thermal.
- **6** Select the **Reverse color table** check box.

# Arrow Surface 1

- I In the Model Builder window, right-click Current and Voltage and choose Arrow Surface.
- 2 In the Settings window for Arrow Surface, click Replace Expression in the upper-right corner of the Expression section. From the menu, choose Component I (compl)> Electric Currents, Single Layer Shell>Currents and charge>ecs.t|x,...,ecs.t|z -Tangential current density (spatial frame).
- 3 Locate the Coloring and Style section. Select the Scale factor check box.
- 4 In the associated text field, type 2e-9.
- 5 Locate the Arrow Positioning section. In the Number of arrows text field, type 3000.
- 6 Locate the Coloring and Style section. From the Color list, choose Blue.
- 7 In the Current and Voltage toolbar, click Plot.

Finally evaluate the current drawn by the device and the output voltage.

#### Global Evaluation 1

I In the Results toolbar, click (8.5) Global Evaluation.

- 2 In the Settings window for Global Evaluation, click Replace Expression in the upper-right corner of the Expressions section. From the menu, choose Component I (compl)> Electric Currents, Single Layer Shell>Terminals>ecs.IO\_I Terminal current A.
- 3 Click Add Expression in the upper-right corner of the Expressions section. From the menu, choose Component I (comp1)>Electric Currents, Single Layer Shell>Terminals> ecs.V0\_2 Terminal voltage V.
- **4** Locate the **Expressions** section. In the table, enter the following settings:

Expression	Unit	Description
ecs.IO_1	mA	Terminal current
ecs.V0_2-ecs.V0_3	mV	Device Output

5 Click **= Evaluate**.

# Appendix — Geometry Modeling Instructions

From the File menu, choose New.

#### NEW

In the New window, click Blank Model.

# ADD COMPONENT

In the Home toolbar, click Add Component and choose 3D.

#### GEOMETRY I

- I In the Settings window for Geometry, locate the Units section.
- 2 From the Length unit list, choose µm.

Work Plane I (wbl)

In the Geometry toolbar, click Work Plane.

Work Plane I (wbl)>Plane Geometry

In the Model Builder window, click Plane Geometry.

Work Plane I (wbl)>Square I (sql)

- I In the Work Plane toolbar, click Square.
- 2 In the Settings window for Square, locate the Size section.
- 3 In the Side length text field, type 1200.
- 4 Locate the Position section. From the Base list, choose Center.

- 5 In the yw text field, type 478.
- **6** Click to expand the **Layers** section. In the table, enter the following settings:

Layer name	Thickness (µm)
Layer 1	100

- 7 Select the Layers to the left check box.
- 8 Select the Layers to the right check box.
- **9** Select the **Layers on top** check box.

Work Plane I (wb I)>Square 2 (sq2)

- I In the Work Plane toolbar, click Square.
- 2 In the Settings window for Square, locate the Size section.
- 3 In the Side length text field, type 22.6.
- **4** Locate the **Position** section. From the **Base** list, choose **Center**.

Work Plane I (wbl)>Rectangle I (rl)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- 3 In the Width text field, type 52.5.
- **4** In the **Height** text field, type 10.
- **5** Locate the **Position** section. From the **Base** list, choose **Center**.
- **6** Locate the **Rotation Angle** section. In the **Rotation** text field, type 45.
- 7 Click to expand the **Layers** section. In the table, enter the following settings:

Layer name	Thickness (µm)
Layer 1	6.25

- 8 Select the Layers to the right check box.
- 9 Select the Layers to the left check box.
- 10 Clear the Layers on bottom check box.

Work Plane I (wp I)>Rectangle 2 (r2)

- I Right-click Component I (compl)>Geometry I>Work Plane I (wpl)>Plane Geometry> Rectangle I (rI) and choose Duplicate.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- 3 In the Width text field, type 62.5.

- 4 In the Height text field, type 20.
- 5 Locate the Rotation Angle section. In the Rotation text field, type -45.
- **6** Locate the **Layers** section. In the table, enter the following settings:

Layer name	Thickness (µm)
Layer 1	11.25

Work Plane I (wp I)>Rectangle 3 (r3)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- **3** In the **Width** text field, type 210.
- 4 In the **Height** text field, type 140.
- **5** Locate the **Position** section. From the **Base** list, choose **Center**.
- 6 In the yw text field, type -15.

Work Plane I (wp I)>Rectangle 4 (r4)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- 3 In the Width text field, type 40.
- 4 In the Height text field, type 50.
- **5** Locate the **Position** section. In the **xw** text field, type -105.
- 6 In the yw text field, type -35.

Work Plane I (wb I)>Rectangle 5 (r5)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- 3 In the Width text field, type 90.
- 4 In the Height text field, type 40.
- **5** Locate the **Position** section. In the **xw** text field, type -105.
- 6 In the yw text field, type 15.

Work Plane I (wp I)>Rectangle 6 (r6)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- 3 In the Width text field, type 90.
- 4 In the **Height** text field, type 40.

- **5** Locate the **Position** section. In the **xw** text field, type -105.
- 6 In the yw text field, type -85.

Work Plane I (wp I)>Rectangle 7 (r7)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- 3 In the Width text field, type 40.
- 4 In the **Height** text field, type 30.
- **5** Locate the **Position** section. In the **xw** text field, type -55.
- 6 In the yw text field, type -45.

Work Plane I (wpl)>Mirror I (mirl)

- I In the Work Plane toolbar, click Transforms and choose Mirror.
- 2 Select the objects r4, r5, r6, and r7 only.
- 3 In the Settings window for Mirror, locate the Input section.
- 4 Select the **Keep input objects** check box.

Form Composite Faces I (cmfl)

- I In the Model Builder window, under Component I (compl)>Geometry I right-click Work Plane I (wpI) and choose Virtual Operations>Form Composite Faces.
- 2 On the object fin, select Boundaries 19, 20, 26–35, and 38 only.

Form Composite Faces 2 (cmf2)

- I In the Geometry toolbar, click \to \text{Virtual Operations} and choose Form Composite Faces.
- **2** On the object **cmf1**, select Boundaries 11, 14–18, 25, 27, and 32–35 only.

Ignore Edges I (ige I)

- I In the Geometry toolbar, click \times \text{Virtual Operations} and choose Ignore Edges.
- 2 On the object cmf2, select Edges 24 and 94 only.
- 3 In the Settings window for Ignore Edges, locate the Input section.
- 4 Clear the Ignore adjacent vertices check box.

Form Composite Faces 3 (cmf3)

- In the Geometry toolbar, click Virtual Operations and choose Form Composite Faces.
- 2 On the object igel, select Boundaries 7, 12, 15, 17, 21, and 24–26 only.

Ignore Edges 2 (ige2)

I In the Geometry toolbar, click \to Virtual Operations and choose Ignore Edges.

**2** On the object **cmf3**, select Edges 4, 6, 8, 12, 84, and 87–89 only.

#### Piezoresistor

- I In the Geometry toolbar, click \( \frac{1}{2} \) Selections and choose Explicit Selection.
- 2 In the Settings window for Explicit Selection, type Piezoresistor in the Label text field.
- 3 Locate the Entities to Select section. From the Geometric entity level list, choose Boundary.
- 4 On the object ige2, select Boundary 9 only.

# Connections

- I In the Geometry toolbar, click \( \frac{1}{2} \) Selections and choose Explicit Selection.
- 2 In the Settings window for Explicit Selection, type Connections in the Label text field.
- 3 Locate the Entities to Select section. From the Geometric entity level list, choose Boundary.
- **4** On the object **ige2**, select Boundaries 3, 5, 6, 8, 13–15, and 18 only.

# Membrane

- I In the Geometry toolbar, click \( \frac{1}{2} \) Selections and choose Box Selection.
- 2 In the Settings window for Box Selection, type Membrane in the Label text field.
- 3 Locate the Geometric Entity Level section. From the Level list, choose Boundary.
- 4 Locate the **Box Limits** section. In the **x minimum** text field, type -501.
- 5 In the x maximum text field, type 501.
- 6 In the y minimum text field, type -30.
- 7 In the y maximum text field, type 1000.
- 8 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.

#### Model Boundaries

- I In the Geometry toolbar, click \( \frac{1}{2} \) Selections and choose Union Selection.
- 2 In the Settings window for Union Selection, type Model Boundaries in the Label text field.
- **3** Locate the **Geometric Entity Level** section. From the **Level** list, choose **Boundary**.
- **4** Locate the **Input Entities** section. Click + **Add**.
- 5 In the Add dialog box, in the Selections to add list, choose Connections and Membrane.
- 6 Click OK.

# Electric currents

- I In the Geometry toolbar, click \( \frac{1}{2} \) Selections and choose Union Selection.
- 2 In the Settings window for Union Selection, type Electric currents in the Label text field.
- 3 Locate the Geometric Entity Level section. From the Level list, choose Boundary.
- **4** Locate the **Input Entities** section. Click + **Add**.
- 5 In the Add dialog box, in the Selections to add list, choose Piezoresistor and Connections.
- 6 Click OK.

# Fixed Edges

- I In the Geometry toolbar, click **Selections** and choose Adjacent Selection.
- 2 In the Settings window for Adjacent Selection, type Fixed Edges in the Label text field.
- 3 Locate the Input Entities section. From the Geometric entity level list, choose Boundary.
- 4 Click + Add.
- 5 In the Add dialog box, select Membrane in the Input selections list.
- 6 Click OK.
- 7 In the Settings window for Adjacent Selection, locate the Output Entities section.
- 8 From the Geometric entity level list, choose Adjacent edges.

# Fixed Boundaries

- I In the Geometry toolbar, click \( \frac{1}{2} \) Selections and choose Difference Selection.
- 2 In the Settings window for Difference Selection, type Fixed Boundaries in the Label text field.
- 3 Locate the Geometric Entity Level section. From the Level list, choose Boundary.
- **4** Locate the **Input Entities** section. Click **Add**.
- 5 In the Add dialog box, select Model Boundaries in the Selections to add list.
- 6 Click OK.
- 7 In the Settings window for Difference Selection, locate the Input Entities section.
- 8 Click + Add.
- 9 In the Add dialog box, select Membrane in the Selections to subtract list.
- IO Click OK.